Complementary Silicon Power Transistors

- ... designed for general–purpose switching and amplifier applications.
- DC Current Gain hFE = 20-70 @ IC = 4 Adc
- Collector–Emitter Saturation Voltage VCE(sat) = 1.1 Vdc (Max) @ IC = 4 Adc
- Excellent Safe Operating Area

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	60	Vdc
Collector–Emitter Voltage	VCER	70	Vdc
Collector-Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EB}	7	Vdc
Collector Current — Continuous	IC	15	Adc
Base Current	ΙΒ	7	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	115 0.657	Watts W/°C
Operating and Storage Junction Temperature Range	TJ, T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta$ JC	1.52	°C/W

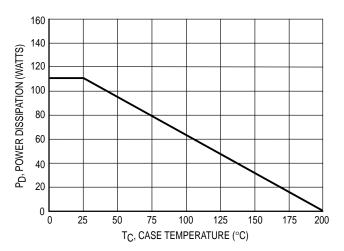


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

NPN 2N3055* PNP * MJ2955

*Motorola Preferred Device

15 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
60 VOLTS
115 WATTS



CASE 1-07 TO-204AA (TO-3)



2N3055 MJ2955

ELECTRICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) (I _C = 200 mAdc, I _B = 0)	VCEO(sus)	60	_	Vdc	
Collector–Emitter Sustaining Voltage (1) (I _C = 200 mAdc, R _{BE} = 100 Ohms)	VCER(sus)	70	_	Vdc	
Collector Cutoff Current (V _{CE} = 30 Vdc, I _B = 0)	ICEO	_	0.7	mAdc	
Collector Cutoff Current (VCE = 100 Vdc, VBE(off) = 1.5 Vdc) (VCE = 100 Vdc, VBE(off) = 1.5 Vdc, T _C = 150°C)	ICEX		1.0 5.0	mAdc	
Emitter Cutoff Current $(V_{BE} = 7.0 \text{ Vdc}, I_{C} = 0)$	I _{EBO}	_	5.0	mAdc	
ON CHARACTERISTICS (1)					
DC Current Gain (IC = 4.0 Adc, VCE = 4.0 Vdc) (IC = 10 Adc, VCE = 4.0 Vdc)	hFE	20 5.0	70 —	_	
Collector–Emitter Saturation Voltage (I _C = 4.0 Adc, I _B = 400 mAdc) (I _C = 10 Adc, I _B = 3.3 Adc)	VCE(sat)	_	1.1 3.0	Vdc	
Base–Emitter On Voltage (I _C = 4.0 Adc, V _{CE} = 4.0 Vdc)	VBE(on)	_	1.5	Vdc	
SECOND BREAKDOWN					
Second Breakdown Collector Current with Base Forward Biased (V _{CE} = 40 Vdc, t = 1.0 s, Nonrepetitive)	I _{s/b}	2.87	_	Adc	
DYNAMIC CHARACTERISTICS					
Current Gain — Bandwidth Product (IC = 0.5 Adc, VCE = 10 Vdc, f = 1.0 MHz)	fΤ	2.5	_	MHz	
*Small–Signal Current Gain (I _C = 1.0 Adc, V _{CE} = 4.0 Vdc, f = 1.0 kHz)	h _{fe}	15	120	_	
*Small–Signal Current Gain Cutoff Frequency (V _{CE} = 4.0 Vdc, I _C = 1.0 Adc, f = 1.0 kHz)	^f hfe	10	_	kHz	

^{*} Indicates Within JEDEC Registration. (2N3055)

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

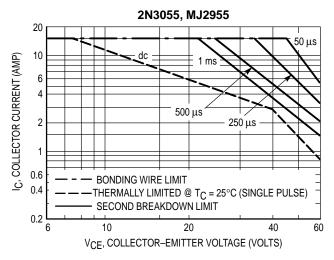


Figure 2. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC – VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C = 25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

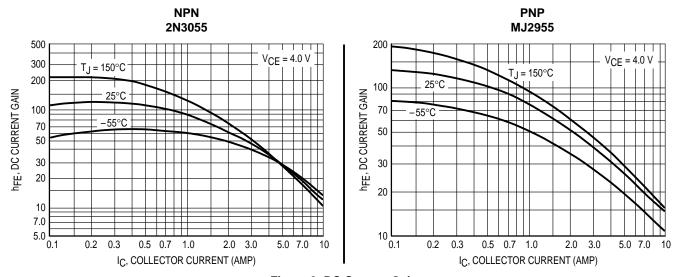


Figure 3. DC Current Gain

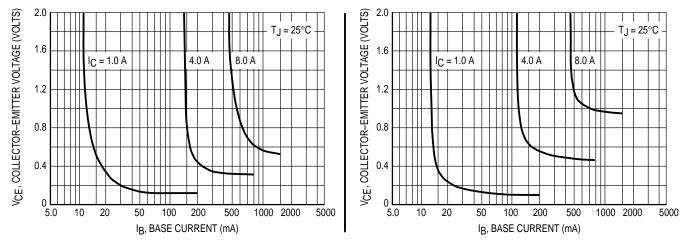


Figure 4. Collector Saturation Region

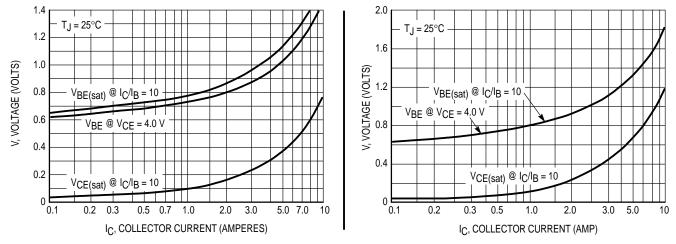
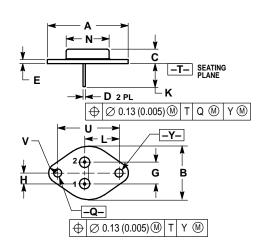


Figure 5. "On" Voltages

PACKAGE DIMENSIONS



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
 - Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 ALL RULES AND NOTES ASSOCIATED WITH
- REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES MILLIMETERS			IETERS
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37 REF	
В		1.050		26.67
U	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
Е	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
Н	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N		0.830		21.08
ď	0.151	0.165	3.84	4.19
5	1.187 BSC		30.15 BSC	
٧	0.131	0.188	3.33	4.77

STYLE 1:

PIN 1. BASE 2. EMITTER CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) ISSUE Z

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2N3055/D

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